Market of the power modules will widely spread towards the various applications such as green energy generation and electric vehicle as well as widely used inverters. Until now, Fuji Electric has been responded to the market demand for the power modules. In future, required performance for them is going to be advanced depending on the wider market. It is important to pay attention to the reliability to respond for these demands.

In this section, reliability for power modules, especially IGBT modules, will be expresses.
Basis of the reliability

Time-dependent change of the failure rate for electronics parts and components including power modules is shown in Fig.1. Generally, it is described a curve like bathtub. There are three durations of early failures, random failures and wear-out failures in this failure rate curve.

Fig.1 Time-dependent change of the failure rate for semiconductor devices

Early failures in IGBT modules would be caused by microscopic defects or human errors, which are originated defects in IGBTs and FWDs, cracking in DCBs, touch of gate and emitter wiring and so on. Continuing the quality improvement activity can reduce such defects or errors. However, since complete removal of them cannot be avoided, removing the early failures is needed. They can be removed by suitable screening condition at outgoing tests. Fuji electric is continuing to prevent outflow of the early failures by suitable outgoing test.

Failure rate of random failures is almost fixed by removing the early failures. Duration of random failure is varied on operating condition or under environments of whole systems composed of IGBT modules and other components. This means that failure rate of random failures is equivalent to the system-specific reliability. Therefore, random failures are in general caused by excessive stresses over maximum rating such as overvoltage, overcurrent, overheat and so on. The various reliability tests have been performed to decrease failure rates during random failure, result in confirming the designs.

The failure during wear-out failures can be not serious because it is caused by wear or fatigue of the products.

IGBT module products need to be selected so as to reach the required life within wear-out duration. Even if IGBT modules were fabricated on the similar condition, life is varied depending on the operating conditions or environments. In addition, it is varied by margin including in operating condition or design. Therefore, IGBT modules on the systems must be selected by taking the operating condition and reliability into consideration.
Chapter 11  Reliability of power module

2  Reliability test condition

As described in the previous section, the various reliability tests have been performed to decrease failure rates during random failure, resulting in confirming the designs.

Tables 1-1 and 1-2 show some parts of representative reliability test condition for the six-generation V-IGBTs. These conditions are governed by JEITA. Refer to the specification sheets in details.

<table>
<thead>
<tr>
<th>Test categories</th>
<th>Test items</th>
<th>Test methods and conditions</th>
<th>Reference norms</th>
<th>Number of sample</th>
<th>Acceptance number</th>
</tr>
</thead>
<tbody>
<tr>
<td>Environment Tests</td>
<td>High Temperature Storage</td>
<td>Storage temp. : 125±5 °C   Test duration : 1000hr.</td>
<td>Test Method 201</td>
<td>5</td>
<td>(0 : 1)</td>
</tr>
<tr>
<td></td>
<td>Low Temperature Storage</td>
<td>Storage temp. : -40±5 °C   Test duration : 1000hr.</td>
<td>Test Method 202</td>
<td>5</td>
<td>(0 : 1)</td>
</tr>
<tr>
<td></td>
<td>Temperature Humidity Storage</td>
<td>Storage temp. : 85±2 °C   Relative humidity : 85±5%   Test duration : 1000hr.</td>
<td>Test Method 103 Test code C</td>
<td>5</td>
<td>(0 : 1)</td>
</tr>
<tr>
<td></td>
<td>Unsaturated Pressurized Vapor</td>
<td>Test temp. : 120±2 °C   Test humidity : 85±5%  Test duration : 96hr.</td>
<td>Test Method 103 Test code E</td>
<td>5</td>
<td>(0 : 1)</td>
</tr>
<tr>
<td></td>
<td>Temperature Cycle</td>
<td>Test temp. : [Low temp. -40±5 °C] [High temp. 125 ±5 °C] [RT 5 ~ 35 °C]   Dwell time : High ~ RT ~ Low ~ RT 1hr. 0.5hr. 1hr. 0.5hr.   Number of cycles : 100 cycles</td>
<td>Test Method 105</td>
<td>5</td>
<td>(0 : 1)</td>
</tr>
<tr>
<td></td>
<td>Thermal Shock</td>
<td>Test temp. : [High temp. 100 ± 5 °C] [Low temp. 0 ± 5 °C]   Used liquid : Water with ice and boiling water   Dipping time : 5 min. par each temp.   Transfer time : 10 sec.   Number of cycles : 10 cycles</td>
<td>Test Method 307 method I Condition code A</td>
<td>5</td>
<td>(0 : 1)</td>
</tr>
</tbody>
</table>
As shown in table 1-2, both high temperature reverse bias and high temperature bias to gate are confirmed on the condition at junction temperature of 150°C, these results can be guaranteed for operating temperature of 150°C.

<table>
<thead>
<tr>
<th>Test categories</th>
<th>Test items</th>
<th>Test methods and conditions</th>
<th>Reference norms</th>
<th>Number of sample</th>
<th>Acceptance number</th>
</tr>
</thead>
<tbody>
<tr>
<td>Endurance Tests</td>
<td>High temperature Reverse Bias</td>
<td>Test temp. : Tj = 150°C ( -0 °C/+5 °C )</td>
<td>Test Method 101</td>
<td>5</td>
<td>( 0 : 1 )</td>
</tr>
<tr>
<td></td>
<td></td>
<td>Bias Voltage : VC = 0.8×VCES</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>Bias Method : Applied DC voltage to C-E VGE = 0V</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>Test duration : 1000hr.</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>High temperature Bias (for gate)</td>
<td>Test temp. : Tj = 150°C ( -0 °C/+5 °C )</td>
<td>Test Method 101</td>
<td>5</td>
<td>( 0 : 1 )</td>
</tr>
<tr>
<td></td>
<td></td>
<td>Bias Voltage : VC = VGE = +20V or -20V</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>Bias Method : Applied DC voltage to G-E VCE = 0V</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>Test duration : 1000hr.</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>Temperature Humidity Bias</td>
<td>Test temp. : 85±2 °C</td>
<td>Test Method 102</td>
<td>5</td>
<td>( 0 : 1 )</td>
</tr>
<tr>
<td></td>
<td></td>
<td>Relative humidity : 85±5%</td>
<td>Condition code C</td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>Bias Voltage : VC = 0.8×VCES</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>Bias Method : Applied voltage to C-E VGE = 0V</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>Test duration : 1000hr.</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td>Intermitted Operating Life (Power cycle) ( for IGBT )</td>
<td>ON time : 2 sec.</td>
<td>Test Method 106</td>
<td>5</td>
<td>( 0 : 1 )</td>
</tr>
<tr>
<td></td>
<td></td>
<td>OFF time : 18 sec.</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>Test temp. : 100±5 deg</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>Tj ≤ 150 °C, Ta=25±5 °C</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>Number of cycles : 15000 cycles</td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>
The temperature of IGBT module rises and falls according to the operating conditions. The interior structure of the IGBT module is exposed to the heat stress caused by this temperature rise and fall and suffers fatigue and deterioration. This fatigue and deterioration depend heavily on the change width of temperature rise and fall and so the life span of the IGBT modules varies depending on the operating and environmental conditions. This heat cycle life is called power cycle life (power cycle capability). The power cycle life can be calculated from the power cycle capability curve that shows the relation between the temperature change $\Delta T$ and the number of cycles, and there are two types of curve.

One is the $\Delta T_j$ power cycle ($\Delta T_j$-P/C) capability curve, which is the life curve made when the element temperature rises and falls suddenly. In this curve, a failure caused by deterioration of the aluminum wire joints on the chip surface becomes predominant. The other is the $\Delta T_c$ power cycle ($\Delta T_c$-P/C) capability curve, which is the life curve made when the change of the case temperature (mainly the copper base plate temperature) follows the temperature rise and fall of the element. In this case, in this curve, a failure caused by deterioration of the soldered joints between the insulated substrate DCB and the copper base plate becomes predominant.

The following sections describe the measurement method and the power cycle capability curve for the $\Delta T_j$-P/C and $\Delta T_c$-P/C power cycles, respectively.

### 3.1 $\Delta T_j$ power cycle ($\Delta T_j$-P/C) capability curve

Figure 11-2 shows the pattern of current flow in the $\Delta T_j$ power cycle ($\Delta T_j$-P/C) test. Figures 11-3 and 11-4 show the equivalent circuit schematic in the $\Delta T_j$ power cycle test and the schematic view of the $T_c$ and $T_f$ measurement positions, respectively. During the $\Delta T_j$ power cycle test, the temperature of the element joints is increased and decreased in a short-time cycle. Therefore, a difference is made in temperature between the silicon chip and the DCB or between the silicon chip and the aluminum wire and so heat stress is caused between them. For this reason, the $\Delta T_j$ power cycle shows mainly the life span of the aluminum wire joints and the soldered section under the chip.

![Pattern diagram of current flow of $\Delta T_j$ power cycle and temperature change](image-url)
Chapter 11  Reliability of power module

Figure 11-5 shows the curves of U series and V series as an example of $\Delta T_j$ power cycle capability curve of the IGBT module. In this figure, the $T_j(\text{min})=25°C$ line indicates the life cycle when the chip temperature is changed while the temperature of the cooling fin is kept at 25°C. For example, when $\Delta T_j = 50°C$, the chip temperature reaches 75°C while the cooling fin temperature is 25°C. On the other hand, the $T_j(\text{max})=150°C$ line shows the life cycle when the temperature of cooling fin is changed while the achieving temperature of the chip is kept at 150°C. For example, when $\Delta T_j = 50°C$, the chip temperature reaches 150°C while the temperature of the cooling fin is 100°C. As shown, even if $\Delta T_j$ is the same, the higher the temperature of the cooling fin and the achieving temperature of the chip are, the shorter the life span is.

---

Fig. 11-3  Equivalent circuit for $\Delta T_j$ power cycle test

Fig. 11-4  Schematic view of $T_c$ and $T_f$ measurement positions

Fig. 11-5  Example of $\Delta T_j$ power cycle capability curve

(F(t) = 1%. Chips connected in parallel are excluded. The dotted lines indicate the expected life span.)
For safe life design of the IGBT module in actual equipment, check $\Delta T_j$ in the operating conditions of the equipment and make sure that the power cycle life, which is obtained from the $\Delta T_j$ power cycle capability curve, is longer enough than the required life span of the product.

For example, as shown in Figure 11-6, in equipment, in which the motor is accelerated, decelerated, started and stopped repeatedly, obtain the $\Delta T_j$ power cycle life where $\Delta T_j$ is the difference between the maximum junction temperature $T_j$ and the fin temperature $T_f$ (see Figure 11-2), and make sure that its life is longer enough than the targeted life span of the product.

For life design in such operating conditions, however, do not obtain $\Delta T_j$ during steady operation. This is because the temperature change caused while the motor is accelerated, decelerated, started and stopped is bigger than the one caused while it is operated steadily, and the life span is affected by such temperature change.

In addition, since the temperature change becomes bigger in a drive system, in which low speed operation such as 0.5Hz is performed, be careful enough of $\Delta T_j$ during the operation when you design the product life.

If there are multiple acceleration, deceleration or low-speed operation temperatures within one operation cycle of the equipment, calculate the power cycle life according to the “Calculation of power cycle life when there are multiple temperature rises in one operation cycle” described later.

Fig. 11-6  Operation in actual inverter (example)
3.2 ΔTc power cycle (ΔTc-P/C) capability curve

Figure 11-7 shows the current flow pattern of ΔTc power cycle (ΔTc-P/C) conducted by us. Figure 11-8 shows the equivalent circuit schematic in the ΔTc power cycle test for the 6in1 module. During the ΔTc power cycle test, all the phases (6 phases in the 6in1 module, and 2 phases in the 2in1 module) are energized, and the temperature of the entire case (mainly the copper base) is increased and decreased. However, the case temperature Tc is increased and decreased in a relatively long-time cycle so that the difference between the junction temperature Tj and the case temperature Tc becomes small. This is different from the conditions in the ΔTj power cycle test. When such temperature change occurs, the significant stress strain becomes predominant between the base and the insulated substrate DCB and so the power cycle shows mainly the life span of the soldered joints under the insulated substrate DCB.

The failure mode of the ΔTc power cycle can be explained as follows. When the case temperature Tc is increased and decreased, the largest stress strain is caused in the soldered joint between the insulated substrate DCB and the base due to the difference in thermal expansion coefficient between them. When this heat change is repeated, the soldered joint is cracked due to the stress strain. When this crack advances up to the lower part of the insulated substrate DCB, on which the silicon chip is installed, the chip junction temperature Tj rises because the heat radiation of the silicon chip is deteriorated (the thermal resistance Rth increases). As a result, the chip junction temperature Tj may exceed Tj(max) and thermal destruction may result.

Figure 11-9 shows the ΔTc power cycle curve in the IGBT module. When the temperature difference between the junction temperature Tj and the case temperature Tc is small and the temperature of the case rises and falls repeatedly, make sure in design that the operation life of the module, which is obtained from the ΔTc power cycle curve, is longer enough than the targeted design life of the product.
1. The definition of the failure criteria in this test is at \( Rth > 1.2 \) times of an initial value.

2. The heat sink used in the test and the mounting condition for the modules is accordance to Fuji standard.

3. The life time curve with black color shown in figure is at \( F(t)=20\% \) of the accumulated failure rate by weibull analysis chart.

4. The life time shown in this figure is the tested results used several type of the modules

5. The dotted line shows the estimated life time.

**Fig. 11-9  Example of \( \Delta Tc \) power cycle capability**

(DCB substrate: \( \text{Al}_2\text{O}_3 \), solder between copper base plate and DCB : Sn type lead-free solder)
3.3 Calculation of power cycle life when there are multiple temperature rises in one operation cycle

The power cycle life of the IGBT module depends on the temperature rise width (and the maximum temperature) during power cycle. Therefore, when there is only one temperature rise peak of the IGBT module in one operation cycle of the inverter, the number of times calculated from the power cycle life curve is the life cycle of the IGBT module.

However, when there are multiple temperature rise peaks in one operation cycle of the inverter, the life cycle becomes shorter because the module is influenced by the multiple temperature rises. The calculation method of power cycle life when there are multiple different temperature rise peaks is shown below.

When there are n times of temperature rises in one operation cycle of inverter, the combined power cycle life can be expressed in the following formula, where PC(k) is the power cycle life for the k-th (k=1, 2, 3, ..., n) temperature rise.

\[
P C = \frac{1}{\sum_{k=1}^{n} \frac{1}{PC(k)}}
\]

For example, when n=4 and the power cycle numbers for the respective power rise peaks are 3.8 x 10^6, 1.2 x 10^6, 7.6 x 10^5 and 4.6 x 10^5, calculation is made as follows:

\[
PC = \frac{1}{\left(\frac{1}{3.8 \times 10^6} + \frac{1}{1.2 \times 10^6} + \frac{1}{7.6 \times 10^5} + \frac{1}{4.6 \times 10^5}\right)} = 2.2 \times 10^5
\]

Therefore, the power cycle lifetime can be obtained from the product of the power cycle life calculated in this way and one cycle (time) of operation mode.

For example, when one cycle of the above operation mode is 1800sec (30min), the lifetime is calculated as follows:

\[
2.2 \times 10^5 \times 1800 / (60 \times 60 \times 24 \times 365) = 12.55 \approx 12 \text{ years and 6 months.}
\]
1. This Catalog contains the product specifications, characteristics, data, materials, and structures as of January 2017. The contents are subject to change without notice for specification changes or other reasons. When using a product listed in this Catalog, be sure to obtain the latest specifications.

2. All applications described in this Catalog exemplify the use of Fuji's products for your reference only. No right or license, either express or implied, under any patent, copyright, trade secret or other intellectual property right owned by Fuji Electric Co., Ltd. is (or shall be deemed) granted. Fuji Electric Co., Ltd. makes no representation or warranty, whether express or implied, relating to the infringement or alleged infringement of other's intellectual property rights which may arise from the use of the applications described herein.

3. Although Fuji Electric Co., Ltd. is enhancing product quality and reliability, a small percentage of semiconductor products may become faulty. When using Fuji Electric semiconductor products in your equipment, you are requested to take adequate safety measures to prevent the equipment from causing a physical injury, fire, or other problem if any of the products become faulty. It is recommended to make your design failsafe, flame retardant, and free of malfunction.

4. The products introduced in this Catalog are intended for use in the following electronic and electrical equipment which has normal reliability requirements.
   - Computers
   - OA equipment
   - Communications equipment (terminal devices)
   - Measurement equipment
   - Machine tools
   - Audiovisual equipment
   - Electrical home appliances
   - Personal equipment
   - Industrial robots etc.

5. If you need to use a product in this Catalog for equipment requiring higher reliability than normal, such as for the equipment listed below, it is imperative to contact Fuji Electric Co., Ltd. to obtain prior approval. When using these products for such equipment, take adequate measures such as a backup system to prevent the equipment from malfunctioning even if a Fuji's product incorporated in the equipment becomes faulty.
   - Transportation equipment (mounted on cars and ships)
   - Trunk communications equipment
   - Traffic-signal control equipment
   - Gas leakage detectors with an auto-shut-off feature
   - Emergency equipment for responding to disasters and anti-burglary devices
   - Safety devices
   - Medical equipment

6. Do not use products in this Catalog for the equipment requiring strict reliability such as the following and equivalents to strategic equipment (without limitation).
   - Space equipment
   - Aeronautical equipment
   - Nuclear control equipment
   - Submarine repeater equipment

7. Copyright ©1996-2011 by Fuji Electric Co., Ltd. All rights reserved. No part of this Catalog may be reproduced in any form or by any means without the express permission of Fuji Electric Co., Ltd.

8. If you have any question about any portion in this Catalog, ask Fuji Electric Co., Ltd. or its sales agents before using the product. Neither Fuji Electric Co., Ltd. nor its agents shall be liable for any injury caused by any use of the products not in accordance with instructions set forth herein.